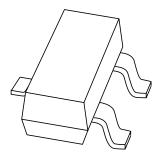
DISCRETE SEMICONDUCTORS

DATA SHEET



BSV52NPN switching transistor

Product data sheet Supersedes data of 1999 Apr 15 2004 Jan 14



NPN switching transistor

BSV52

FEATURES

• Low current (max. 100 mA)

• Low voltage (max. 12 V).

APPLICATIONS

 High speed saturated switching applications, especially in portable equipment.

DESCRIPTION

NPN switching transistor in a SOT23 plastic package.

MARKING

TYPE NUMBER	MARKING CODE ⁽¹⁾		
BSV52	B2*		

Note

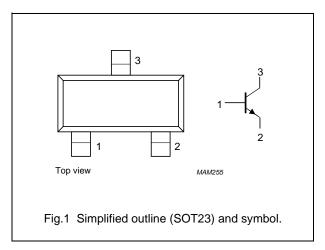
1. * = p: Made in Hong Kong.

* = t : Made in Malaysia.

* = W: Made in China.

PINNING

PIN	DESCRIPTION	
1	base	
2	emitter	
3	collector	



ORDERING INFORMATION

TYPE NUMBER		PACKAGE			
ITPE NUMBER	NAME DESCRIPTION VERSION				
BSV52	-	plastic surface mounted package; 3 leads			

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	_	20	V
V_{CEO}	collector-emitter voltage	open base	_	12	V
V_{EBO}	emitter-base voltage	open collector	_	5	V
I _C	collector current (DC)		_	100	mA
I _{CM}	peak collector current		_	200	mA
I _{BM}	peak base current		_	100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	_	250	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT	
R _{th(j-a)}	thermal resistance from junction to ambient	note 1	500	K/W	

Note

1. Transistor mounted on an FR4 printed-circuit board.

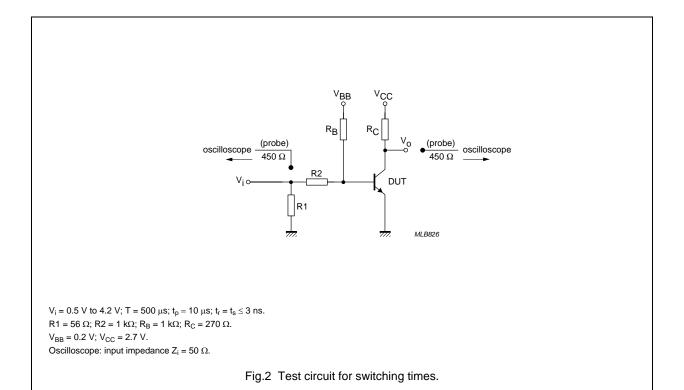
CHARACTERISTICS

 $T_j = 25$ °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{CBO}	collector cut-off current	I _E = 0; V _{CB} = 20 V	-	-	400	nA
		I _E = 0; V _{CB} = 20 V; T _j = 125 °C	-	-	30	μΑ
I _{EBO}	emitter cut-off current	I _C = 0; V _{EB} = 4 V	-	-	100	nA
h _{FE}	DC current gain	V _{CE} = 1 V				
		I _C = 1 mA	25	_	_	
		I _C = 10 mA	40	_	120	
		I _C = 50 mA	25	_	_	
V _{CEsat}	collector-emitter saturation	$I_C = 10 \text{ mA}; I_B = 300 \mu\text{A}$	-	-	300	mV
	voltage	I _C = 10 mA; I _B = 1 mA	-	-	250	mV
		$I_C = 50 \text{ mA}; I_B = 5 \text{ mA}$	-	-	400	mV
V _{BEsat}	base-emitter saturation voltage	I _C = 10 mA; I _B = 1 mA	700	-	850	mV
		$I_C = 50 \text{ mA}; I_B = 5 \text{ mA}$	-	-	1.2	V
C _c	collector capacitance	$I_E = i_e = 0$; $V_{CB} = 5$ V; $f = 1$ MHz	-	_	4	pF
C _e	emitter capacitance	$I_C = I_C = 0$; $V_{EB} = 1 \text{ V}$; $f = 1 \text{ MHz}$	-	_	4.5	pF
f_{T}	transition frequency	$I_C = 10 \text{ mA}; V_{CE} = 10 \text{ V}; f = 100 \text{ MHz}$	400	500	_	MHz
Switching ti	Switching times (between 10% and 90% levels); (see Fig.2)					
t _{on}	turn-on time	I _{Con} = 10 mA; I _{Bon} = 3 mA;	_	_	10	ns
t _d	delay time	$I_{Boff} = -1.5 \text{ mA}$	_	_	4	ns
t _r	rise time		_	-	6	ns
t _{off}	turn-off time		_	-	20	ns
t _s	storage time		_	_	10	ns
t _f	fall time		-	_	10	ns

NPN switching transistor

BSV52

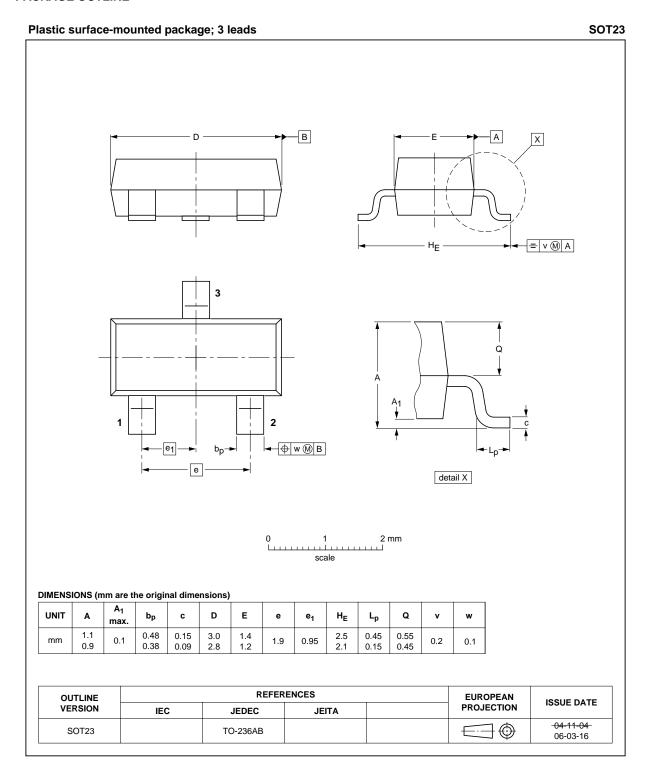


2004 Jan 14

NPN switching transistor

BSV52

PACKAGE OUTLINE



NPN switching transistor

BSV52

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

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Customer notification

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

Contact information

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